



OPTICALLY COUPLED ISOLATOR PHOTOTRANSISTOR OUTPUT

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 approval pending
- EN60950 approval pending

DESCRIPTION

The MOC8100 optically coupled isolator consists of infrared light emitting diode and NPN silicon photo transistor in a standard 6 pin dual in line plastic package.

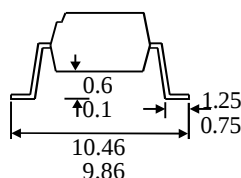
FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- Low Input Current 1mA I_F
- High Current Transfer Ratio (50% min)
- All electrical parameters 100% tested
- Custom electrical selections available

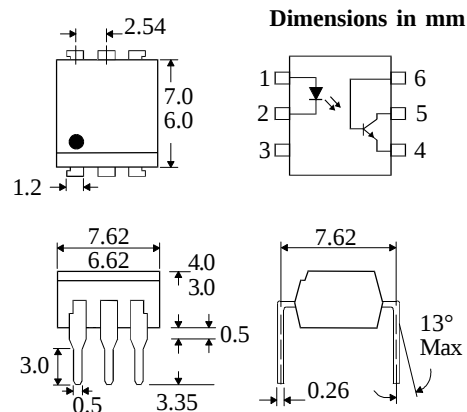
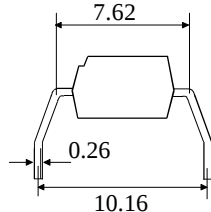
APPLICATIONS

- DC motor controllers
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

OPTION SM SURFACE MOUNT



OPTION G



ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature _____ -55°C to + 150°C
Operating Temperature _____ -55°C to + 100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current _____ 60mA
Reverse Voltage _____ 6V
Power Dissipation _____ 105mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} _____ 30V
Collector-base Voltage BV_{CBO} _____ 70V
Emitter-base Voltage BV_{EBO} _____ 6V
Power Dissipation _____ 160mW

POWER DISSIPATION

Total Power Dissipation _____ 200mW
(derate linearly 2.67mW/°C above 25°C)

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.4	V	$I_F = 10\text{mA}$
	Reverse Voltage (V_R)	6			V	$I_R = 10\mu\text{A}$
	Reverse Current (I_R)			10	μA	$V_R = 6\text{V}$
Output	Collector-emitter Breakdown (BV_{CEO})	30			V	$I_C = 1\text{mA}$ (note 2)
	Collector-base Breakdown (BV_{CBO})	70			V	$I_C = 100\mu\text{A}$
	Emitter-base Breakdown (BV_{EBO})	6			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			25	nA	$V_{CE} = 5\text{V}$
	Collector-base Dark Current (I_{CBO})			10	nA	$V_{CE} = 5\text{V}$
Coupled	Output Collector Current (I_C)	0.5 0.3			mA mA	$1\text{mA } I_F, 5\text{V } V_{CE}$ $1\text{mA } I_F, 5\text{V } V_{CE}$ ($T_A = 0 \text{ to } +70^\circ\text{C}$)
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.5	V	$1\text{mA } I_F, 100\mu\text{A } I_C$
	Input to Output Isolation Voltage V_{ISO}	5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
	Turn-on Time t_{on}			20	μs	$V_{CC} = 10\text{V}, I_C = 2\text{mA}$
	Turn-off Time t_{off}			20	μs	$R_L = 100\Omega$, fig 1
	Output Rise Time t_r		4		μs	$V_{CC} = 10\text{V}, I_C = 2\text{mA}$
	Output Fall Time t_f		6		μs	$R_L = 100\Omega$, fig 1

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

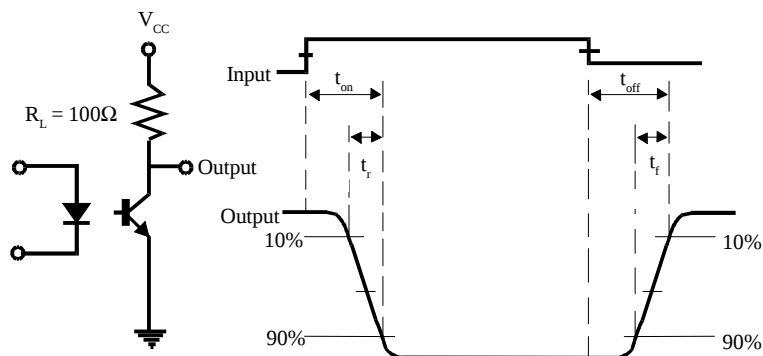
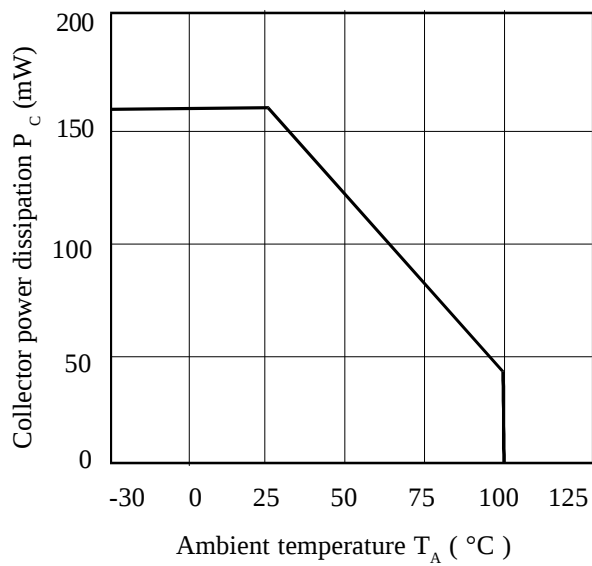
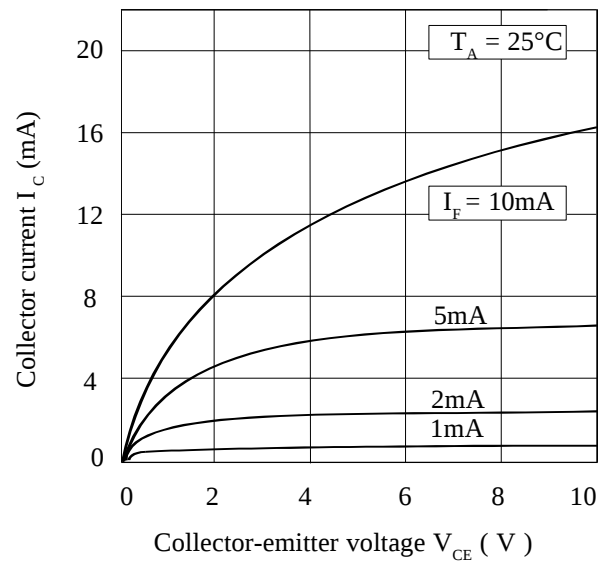


FIG 1

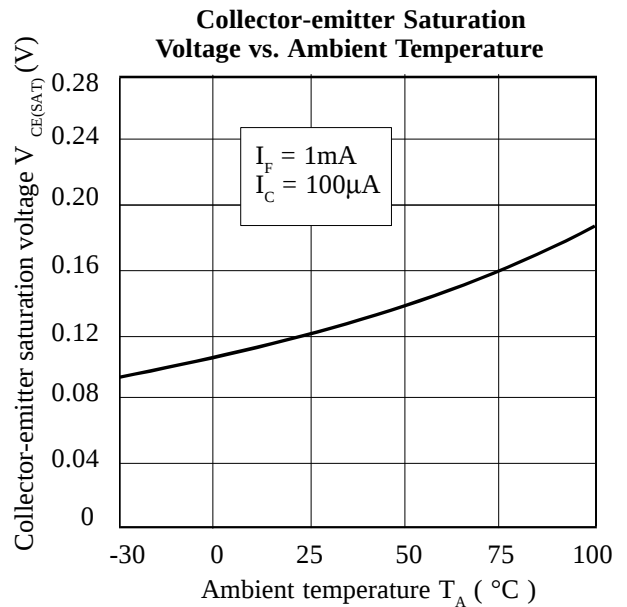
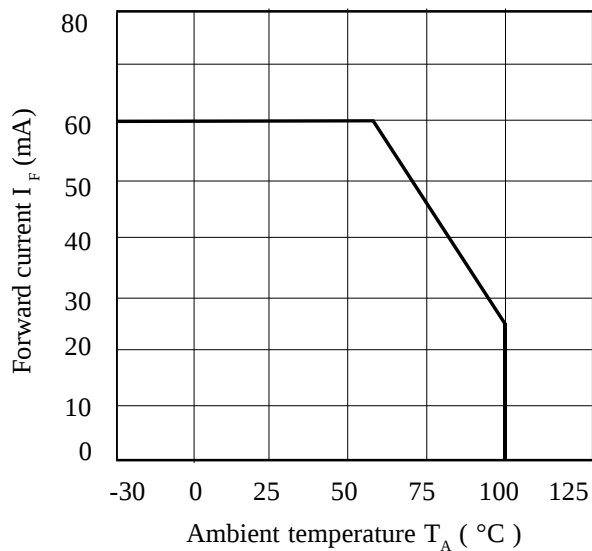
Collector Power Dissipation vs. Ambient Temperature



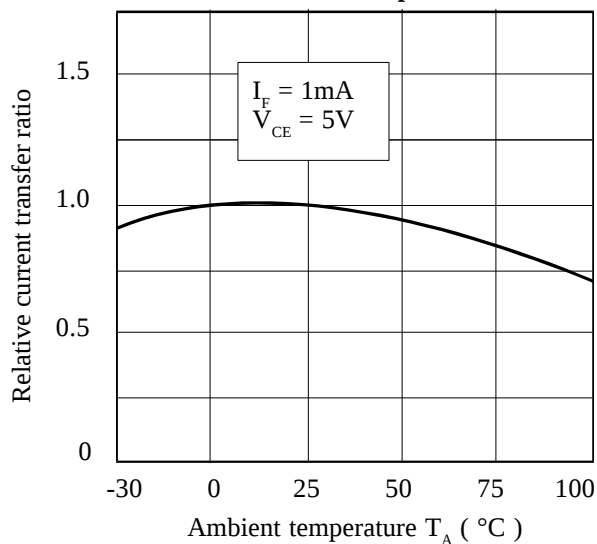
Collector Current vs. Collector-emitter Voltage



Forward Current vs. Ambient Temperature



Relative Current Transfer Ratio vs. Ambient Temperature



Relative Current Transfer Ratio vs. Forward Current

